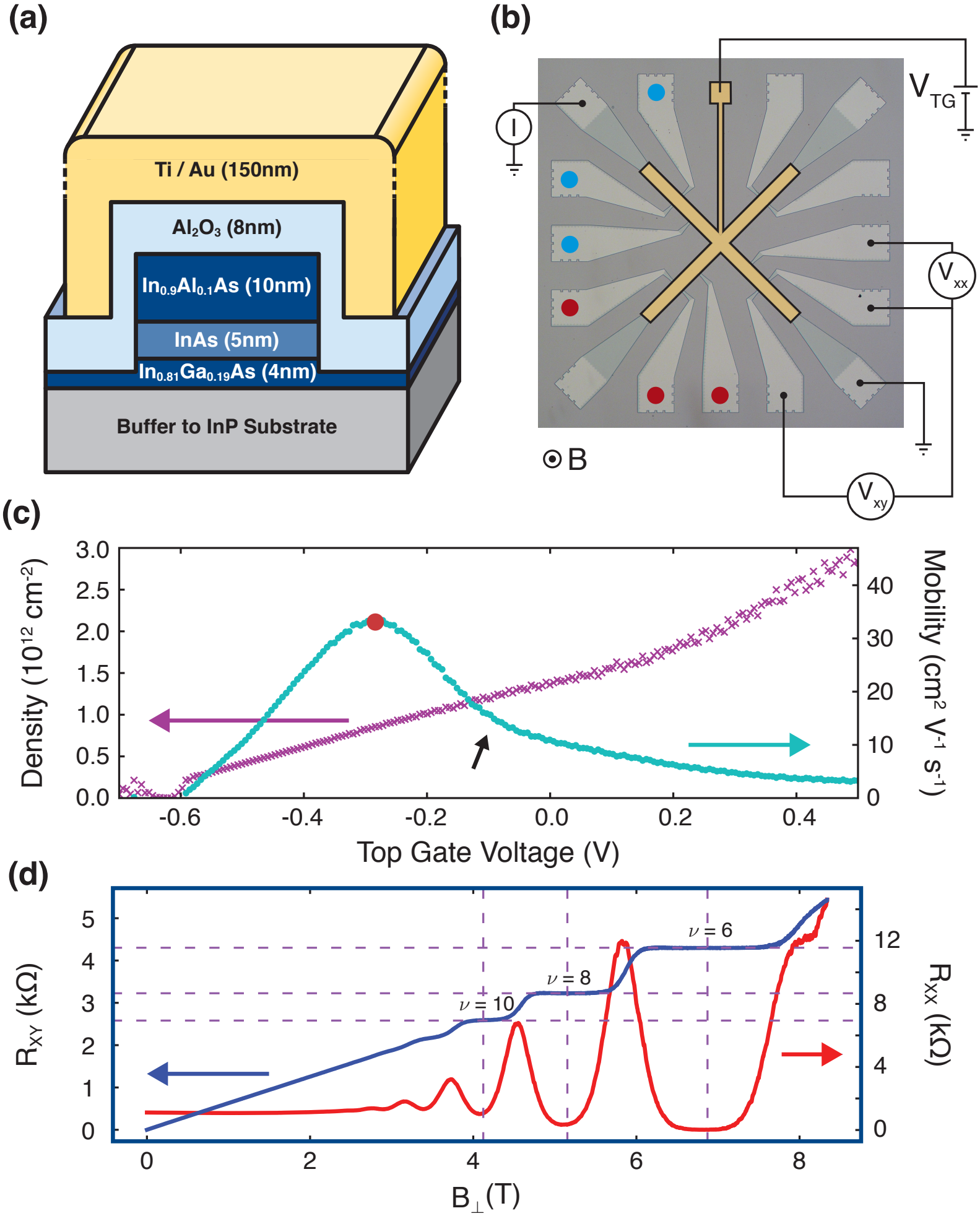
(a)
Ti / Au (150nm)
Al2O3 (8nm)
In0.9Al0.1As (10nm)
InAs (5nm)
In0.81Ga0.19As (4nm)
Buffer to InP Substrate
(b)
I
VTG
Vxx
Vxy
B
(c)
Density (10^12 cm^-2)
Mobility (cm^2 V^-1 s^-1)
Top Gate Voltage (V)
(d)
RXY (kΩ)
Rxx (kΩ)
ν = 10
ν = 8
ν = 6
B⊥ (T)